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(71) Applicant (for all designated States except US): **SEMI-CONDUCTOR ENERGY LABORATORY CO., LTD.**  
[JP/JP]; 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

(72) Inventors; and

(75) Inventors/Applicants (for US only): **ARAI, Yasuyuki**  
[JP/JP]; c/o SEMICONDUCTOR ENERGY LABORA-  
TORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa,

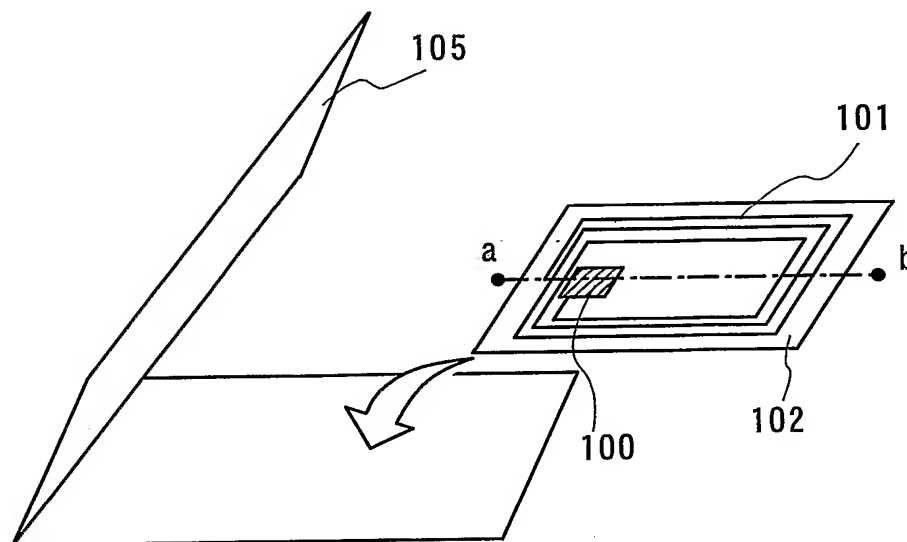
2430036 (JP). **AKIBA, Mai** [JP/JP]; c/o SEMICONDUCTOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP). **KANNO, Yohei** [JP/JP]; c/o SEMICONDUCTOR ENERGY LABORA-  
TORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP). **TACHIMURA, Yuko** [JP/JP]; c/o SEMI-  
CONDUCTOR ENERGY LABORATORY CO., LTD., 398, Hase, Atsugi-shi, Kanagawa, 2430036 (JP).

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(54) Title: FILM-LIKE ARTICLE AND METHOD FOR MANUFACTURING THE SAME



(57) Abstract: Since the chip formed from a silicon wafer is thick, the chip is protruded from the surface or the chip is so large that it can be seen through the eyes, which affects the design of a business card or the like. Hence, it is an object of the present invention to provide a new integrated circuit which has a structure by which the design is not affected. In view of the above problems, it is a feature of the invention to equip a film-like article with a thin film integrated circuit. It is another feature of the invention that the IDF chip has a semiconductor film of 0.2 mm or less, as an active region. Therefore, the IDF chip can be made thinner as compared with a chip formed from a silicon wafer. In addition, such an integrated circuit can have light transmitting characteristic unlike a chip formed from a silicon wafer.

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